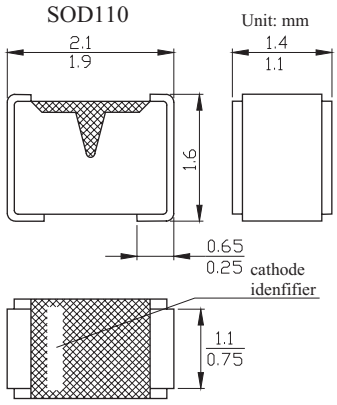
Schottky barrier diode

BAT254



■ Features

- Low forward voltage
- Guard ring protoected
- Very small ceramic SMD package.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Conditions	Min	Max	Unit
Continuous reverse voltage	V_R			30	V
Continuous forward current	I_F			200	mA
Repetitive peak forward current	I_{FSM}	$t_p \leqslant 1s$; $\delta \leqslant 0.5$		300	mA
Non-repetitive peak forwrad current	I_{FSM}	$t_p < 1s$		600	mA
Storage temperature	T_{stg}		-65	+150	℃
Junction temperature	T_j			125	℃
Operating ambient temperature	T_{amb}		-65	+125	℃

Schottky barrier diode

BAT254

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Max	Unit
forward voltage	V_F	I_F = 0.1 mA	240	mV
		I_F = 1 mA	320	
		I_F = 10 mA	400	
		I_F = 30 mA	500	
		I_F = 100 mA	800	
reverse current	I_R	V_R = 25 V, note 1	2	μA
reverse recovery time	t_{rr}	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω measured at I_R = 1 mA	5	ns
diode capacitance	C_d	f = 1 MHz; V_R = 1 V;	10	pF
thermal resistance from junction to ambient	$R_{th\ j\text{-}a}$	note 2	315	K/W

Note

1.Pulsed test: tp = 300 μs, δ = 0.02.

2.Refer to SOD110 standard mounting conditions.

■ Marking

Marking	L4